

DERWENT-ACC-NO: 2001-229584

DERWENT-WEEK: 200124

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TITLE: Semiconductor device manufacture involves forming
indium
gallium phosphide layer on gallium arsenide layer and
etching indium gallium phosphide layer using hydrochloric
acid etching liquid or its aqueous solution

PATENT-ASSIGNEE: NEC CORP[NIDE]

PRIORITY-DATA: 1999JP-0198228 (July 12, 1999)

PATENT-FAMILY:

| PUB-NO | PUB-DATE | LANGUAGE | PAGES |
|-----------------|------------------|----------|---------------------|
| MAIN-IPC | | | |
| JP 2001023951 A | January 26, 2001 | N/A | 007 H01L 021/306 |

APPLICATION-DATA:

| PUB-NO | APPL-DESCRIPTOR | APPL-NO | APPL-DATE |
|---------------|-----------------|----------------|---------------|
| JP2001023951A | N/A | 1999JP-0198228 | July 12, 1999 |

INT-CL (IPC): C09K013/04, H01L021/306 , H01L021/308 , H01L033/00

ABSTRACTED-PUB-NO: JP2001023951A

BASIC-ABSTRACT: